

3600.2406  
October 25, 2002 (1:46PM)

Docket: AM-2406

target and a substrate, comprising:

sputtering the target onto a surface of the substrate at a pressure less than about 15 mTorr;  
collimating sputtering of the target with a grounded collimator disposed between the  
target and the substrate; and  
generating a magnetic field that is substantially parallel to the surface of the substrate  
during sputtering using an annular magnet array concentrically disposed around a perimeter of  
the surface of the substrate within the sputtering chamber.

22. The apparatus of claim 21, wherein the target comprises a material that retains  
magnetic properties when deposited on the surface of a substrate.

23. The apparatus of claim 23, wherein the target is separated from the substrate support  
by a distance of at least 50 mm.

24. The apparatus of claim 21, wherein the annular magnet array comprises a plurality of  
magnetic segments positioned in an annular configuration around the perimeter of the substrate  
support, the plurality of magnetic segments having different magnetic orientations that  
cooperatively combined to magnetic field that is parallel to the substrate surface.

25. The apparatus of claim 23, wherein the target comprises a nickel/iron alloy.

26. The apparatus of claim 21 wherein the target and the substrate supporting surface are  
separated by a distance of at least 50 mm.

27. A method for depositing a magnetic film within a sputtering chamber containing a  
target and a substrate, comprising:

sputtering the target onto a surface of the substrate at a pressure less than about 15 mTorr;

3600.2406  
October 25, 2002 (1:46PM)

Docket: AM-2406

collimating sputtering of the target with a grounded collimator disposed between the target and the substrate; and

generating a magnetic field that is substantially parallel to the surface of substrate during sputtering using an annular magnet array concentrically disposed around a perimeter of the surface of the substrate within the sputtering chamber.

28. The method of claim 27, wherein the sputtering occurs at a chamber pressure less than about 5 mTorr.

29. The method of claim 27, wherein the target and the surface of the substrate are maintained at a distance of at least 50 mm during sputtering.

30. The method of claim 29, wherein the target comprises a Ni/Fe alloy.

31. The method of claim 27, wherein the grounded collimator removes charges from target particles and reduces interference with the parallel magnetic field.

32. (New) The apparatus of claim 21, wherein said magnetic field at said substrate surface is substantially parallel to said substrate surface.

33. (New) The apparatus of Claim 21, wherein said annular magnet array comprises a plurality of permanent magnets.

34. (New) The apparatus of Claim 33, wherein said plurality of permanent magnets are magnetized parallel to a plane of said substrate surface

35. (New) The apparatus of Claim 21, wherein said annular magnet array is a Halbach

3600.2406  
October 25, 2002 (1:46PM)

Docket: AM-2406

array.

36. (New) The method of Claim 27 wherein said target comprises a material that is magnetic when sputter deposited in a substantially parallel magnetic field.

37. (New) The method of Claim 27, wherein said annular magnet array comprises an array of permanent magnets magnetized parallel to a plane of the surface of the substrate during sputtering.

38. (New) The method of Claim 27, wherein said annular magnet array comprises a Halbach array.

39. (New) The method of Claim 27, wherein said magnetic field at the surface of the substrate is substantially parallel to the surface of said substrate.

40. (New) The method of Claim 27, wherein the substrate is processed to form a magnetic recording head.